

Continental Device India Limited An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company



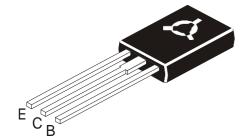
BD140

TO126

BD136 BD138

Plastic Package

PNP EPITAXIAL SILICON POWER TRANSISTORS



Designed for use as Audio Amplifier and Drivers Utilizing

Complementary BD135, BD137, BD139

ABSOLUTE MAXIMUM RATINGS

| DESCRIPTION | SYMBOL | BD136 | BD138 | BD140 | UNIT |
|---|-----------------------------------|--------------|-------|-------|-------|
| Collector -Emitter Voltage | V _{CEO} | 45 | 60 | 80 | V |
| Collector -Emitter Voltage (R _{BE} =1kW) | V _{CER} | 45 | 60 | 100 | V |
| Collector -Base Voltage | V _{CBO} | 45 | 60 | 100 | V |
| Emitter Base Voltage | V _{EBO} | · | V | | |
| Collector Current | lc | | А | | |
| Collector Peak Current | I _{CM} | | 2.0 | | А |
| Base Current | Ι _Β | | 0.5 | | A |
| Power Dissipation @ T _a =25 ^o C | PD | 1.25 | | | W |
| Derate above 25°C | | | 10 | | mW/ºC |
| Power Dissipation @ Tc=25°C | PD | 12.5 | | | W |
| Derate above 25°C | | | mW/ºC | | |
| Power Dissipation @ T _c =70 ^o C | PD | | W | | |
| Operating and Storage Junction Temperature Range | T _j , T _{stg} | - 55 to +150 | | | |

THERMAL CHARACTERISTICS

| Junction to Ambient in free air | R _{th (j-a)} | 100 | °C/W |
|---------------------------------|-----------------------|-----|------|
| Junction to Case | R _{th (j-c)} | 10 | °C/W |

ELECTRICAL CHARACTERISTICS (Tc=25°C unless specified otherwise)

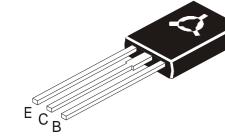
| DESCRIPTION | SYMBOL | TEST CONDITION | MIN | MAX | UNIT |
|--------------------------------------|-------------------------|---|-----|-----|------|
| Collector Emitter Sustaining Voltage | *V _{CEO (sus)} | Ic=30mA, Iв=0 | | | |
| | | BD136 | 45 | | V |
| | | BD138 | 60 | | V |
| | | BD140 | 80 | | V |
| Collector Cut Off Current | I _{CBO} | V _{CB} =30V, I _E =0 | | 0.1 | μΑ |
| | | V _{CB} =30V, I _E =0, T _c =125°C | | 10 | μA |
| Emitter Cut Off Current | I _{EBO} | V _{EB} =5V, I _C =0 | | 10 | μA |
| DC Current Gain | *h _{FE} | Ic=0.005A, Vce=2V | 25 | | |
| | | I _C =0.15A, V _{CE} =2V | 40 | 250 | |
| | | Ic=0.5A, Vce=2V | 25 | | |

*Pulse test:- Pulse width=300ms, duty cycle=2%

PNP EPITAXIAL SILICON POWER TRANSISTORS



BD136 BD138 BD140



TO126 Plastic Package

ELECTRICAL CHARACTERISTICS (T_c=25°C unless specified otherwise)

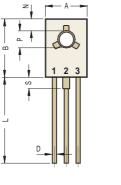
| DESCRIPTION | SYMBOL | TEST CONDITION | MIN | MAX | UNIT |
|--------------------------------------|------------------------|--|-----|-----|------|
| DC Current Gain | *h _{FE} Group | I _C =0.15A, V _{CE} =2V | | | |
| | | - 6 | 40 | 100 | |
| | | - 10 | 63 | 160 | |
| | | - 16 | 100 | 250 | |
| | | - 25 | 160 | 400 | |
| Collector Emitter Saturation Voltage | *V _{CE (sat)} | Ic=0.5A, I _B =0.05A | | 0.5 | V |
| Base Emitter On Voltage | *V _{BE(on)} | *Ic=0.5A, Vce=2V | | 1.0 | V |

*Pulse test:- Pulse width=300ms, duty cycle=2%

BD136 BD138 BD140

TO126 Plastic Package



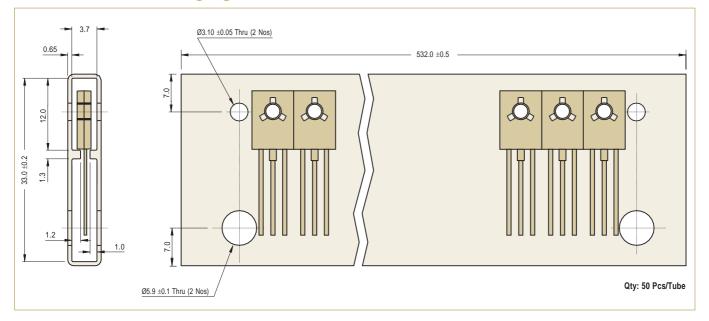


| DIM | Min |
|-----------|---|
| А | 7.12 |
| В | 10.16 |
| С | 2.29 |
| D | 0.64 |
| Е | 2.040 |
| F | 0.39 |
| in Config | jurations |
| | A B C D E F in Config |

| М | Min | Max | DIM | Min | Max |
|---|-------|-------|-----|-------|-------|
| | 7.12 | 8.38 | G | 4.07 | 5.08 |
| | 10.16 | 11.43 | L | 15.00 | 16.63 |
| | 2.29 | 3.04 | М | 0.89 | 1.65 |
|) | 0.64 | 0.88 | Ν | 3.31 | 4.44 |
| | 2.040 | 2.285 | Р | 2.54 | 3.30 |
| | 0.39 | 0.63 | S | — | 2.54 |

Pin 1: Emitter Pin 2: Collector Pin 3: Base

TO-126 Series Packaging Tube



C

Т

Packaging Specifications

| Package / Case Type | Packaging Type | Std. Packing | Inner Carton | | | Outer Carton | | |
|---------------------|----------------|---------------------|--------------|----------------|--------------|--------------|----------------|-------------|
| | | Qty | Qty | Size L x W x H | Gross Weight | Qty | Size L x W x H | Gross Weigh |
| | | | | (cm) | (Kg) | | (cm) | (Kg) |
| TO-126 | Bulk | 2,000 | 2K | 19x19x8 | 1.4 | 20K | 46 x 38 x 22 | 15.6 |
| | Tube | 1,000 (50 pcs/tube) | 1K | 55 x 8 x 10 | 1.5 | 10K | 55 x 35 x 27 | 16.3 |

TO126 Plastic Package

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of Continental Device India Limited

BD136_138_140Rev_2 091002E